

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor laser comprising a GaN-based semiconductor substrate and laminated layers formed on the GaN-based semiconductor substrate which include a GaN-based semiconductor clad layer containing Al and an active layer formed thereabove,

wherein the outermost side surfaces of the laminated layers along the direction of the resonator of the semiconductor laser are inclined with respect to the GaN-based semiconductor substrate in such a direction that a resonator width is decreased from the GaN-based semiconductor substrate side to the upper portion of the laminated layers, and

wherein ~~the laminated layers are rectangular shaped layers in cross section that are stacked on top of one another such that each one of the laminated layers is positioned entirely above an adjacently positioned lower one of the laminated layers and said each one of the laminated layers is positioned entirely below an adjacently positioned upper one of the laminated layers a lowermost layer of the laminated layers has a resonator width of 50 µm or more.~~

2. (Currently Amended) The semiconductor laser according to Claim 1, wherein masks are formed on the GaN-based semiconductor substrate and the laminated layers are formed above the masks so that the side surfaces of the laminated layers along the direction of the resonator are from the grown surfaces of the semiconductor layers which have been selectively grown from the masks, ~~and wherein the outermost side surfaces of the laminated layers are inclined at an angle of about 60 degrees with respect to an upper surface of GaN-based semiconductor substrate that is in contact with a lowest positioned one of the laminated layers.~~

3. (Previously Presented) The semiconductor laser according to Claim 1, wherein the end surfaces of the resonator of the semiconductor laser are cleavage planes of the GaN-based semiconductor substrate and the laminated layers.

4-12. (Cancelled)

13. (New) A semiconductor laser comprising a GaN-based semiconductor substrate and laminated layers formed on the GaN-based semiconductor substrate which include a GaN-based semiconductor clad layer containing Al and an active layer formed thereabove,

wherein the outermost side surfaces of the laminated layers along the direction of the resonator of the semiconductor laser are inclined with respect to the GaN-based semiconductor substrate in such a direction that a resonator width is decreased from the GaN-based semiconductor substrate side to the upper portion of the laminated layers, and the active layer has a width of about 10 μm .